

SML300HB12

Attributes:

- aerospace build standard
- high reliability
- lightweight
- metal matrix base plate
- AlN isolation
- trench gate igbts



Maximum rated values/Electrical Properties

Collector-emitter Voltage		V_{ce}	1200	V
DC Collector Current	$T_c=70C, T_{vj}=175C$ $T_c=25C, T_{vj}=175C$	$I_{c, nom}$ I_c	300 440	A
Repetitive peak Collector Current	$t_p=1msec, T_c=80C$	I_{crm}	600	A
Total Power Dissipation	$T_c=25C$	P_{tot}	2380	W
Gate-emitter peak voltage		V_{ges}	+/-20	V
DC Forward Diode Current		I_f	300	A
Repetitive Peak Forward Current	$t_p=1msec$	I_{frm}	600	A
I^2t value per diode	$V_r=0V, t_p=10msec,$ $T_{vj}=125C$	I^2_t	19000	A^2sec
Isolation voltage	RMS, 50Hz, $t=1min$	V_{isol}	2500	V

Collector-emitter saturation voltage	$I_c=300A, V_{ge}=15V, T_c=25C$ $I_c=300A, V_{ge}=15V, T_c=125C$	$V_{ce(sat)}$		1.7 2.0	2.15	V
Gate Threshold voltage	$I_c=4.8mA, V_{ce}=V_{ge}, T_{vj}=25C$	$V_{ge(th)}$	5.0	5.8	6.5	V
Input capacitance	$f=1MHz, T_{vj}=25C, V_{ce}=25V,$ $V_{ge}=0V$	C_{ies}		21		nF
Reverse transfer Capacitance	$f=1MHz, T_{vj}=25C, V_{ce}=25V,$ $V_{ge}=0V$	C_{res}		0.85		nF
Collector emitter cut off current	$V_{ce}=1200V, V_{ge}=0V, T_{vj}=25C$	I_{ces}		1	5	mA
Gate emitter cut off current	$V_{ce}=0V, V_{ge}=20V, T_{vj}=25C$	I_{ges}			400	nA



Turn on delay time	Ic=300A, Vcc=600V Vge=+/15V,Rg=2.4Ω,Tvj=25C Vge=+/-15V,Rg=2.4Ω,Tvj=125C	t _{d,on}	250 300	nsec nsec nsec
Rise time	Ic=300A, Vcc=600V Vge=+/-15V,Rg=2.4Ω,Tvj=25C Vge=+/-15V,Rg=2.4Ω,Tvj=125C	t _r	90 100	nsec nsec nsec
Turn off delay time	Ic=300A, Vcc=600V Vge=+/-15V,Rg=2.4Ω,Tvj=25C Vge=+/-15V,Rg=2.4Ω,Tvj=125C	t _{d,off}	550 650	nsec nsec nsec
Fall time	Ic=300A, Vcc=600V Vge=+/-15V,Rg=2.4Ω,Tvj=25C Vge=+/-15V,Rg=2.4Ω,Tvj=125C	t _f	130 180	nsec nsec nsec
Turn on energy loss per pulse	Ic=300A, Vce=600V, Vge=+/-15V Rge=2.4Ω, L=30nH Tvj=25C di/dt=6000A/μsec Tvj=125C	E _{on}	17 25	mJ mJ
Turn off energy loss per pulse	Ic=300A, Vce=600V, Vge=+/-15V Rge=2.4Ω, L=30nH Tvj=25C di/dt=4000A/μsec Tvj=125C	E _{off}	29.5 44.0	mJ mJ
SC Data	tp≤10μsec, Vge≤15V Vcc=900V, Vce(max)=Vces-Lσdi/dt Tvj=125C	I _{sc}	1200	A
Stray Module inductance		L _{σcc}	30	nH
Terminal-chip resistance		R _c	1.0	mΩ

Diode characteristics

Forward voltage	Ic=300A, Vge=0V, Tc=25C Ic=300A, Vge=0V, Tc=125C	V _f	1.65 1.65	2.15 V
Peak reverse recovery current	If=300A, -di/dt=6000A/μsec Vce=300V, Vge=-15V, Tvj=25C Vce=300V, Vge=-15V, Tvj=125C	I _{rm}	210 270	A A
Recovered charge	If=300A, -di/dt=6000A/μsec Vce=300V, Vge=-15V, Tvj=25C Vce=300V, Vge=-15V, Tvj=125C	Q _r	30 56	μC μC
Reverse recovery energy	If=300A, -di/dt=6000A/μsec Vce=300V, Vge=-15V, Tvj=25C Vce=300V, Vge=-15V, Tvj=125C	E _{rec}	14 26	mJ mJ



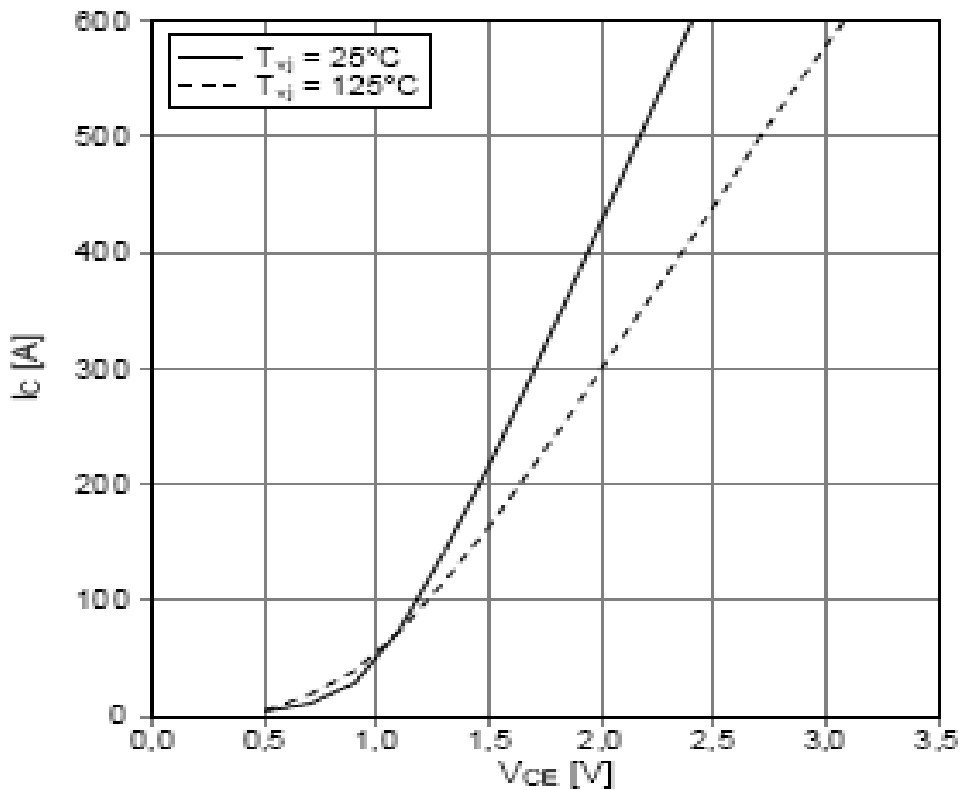
Thermal Properties

			Min	Typ	Max	
Thermal resistance junction to case	Igibt Diode	$R_{\theta J-C}$			0.063 0.11	K/W
Thermal resistance case to heatsink		$R_{\theta C-HS}$		0.03		K/W
Maximum junction temperature		T_{vj}			175	C
Maximum operating temperature		Top	-55		175	C
Storage Temperature		Tstg	-55		175	C

output characteristic IGBT-Inverter (typical)

$$I_C = f(V_{CE})$$

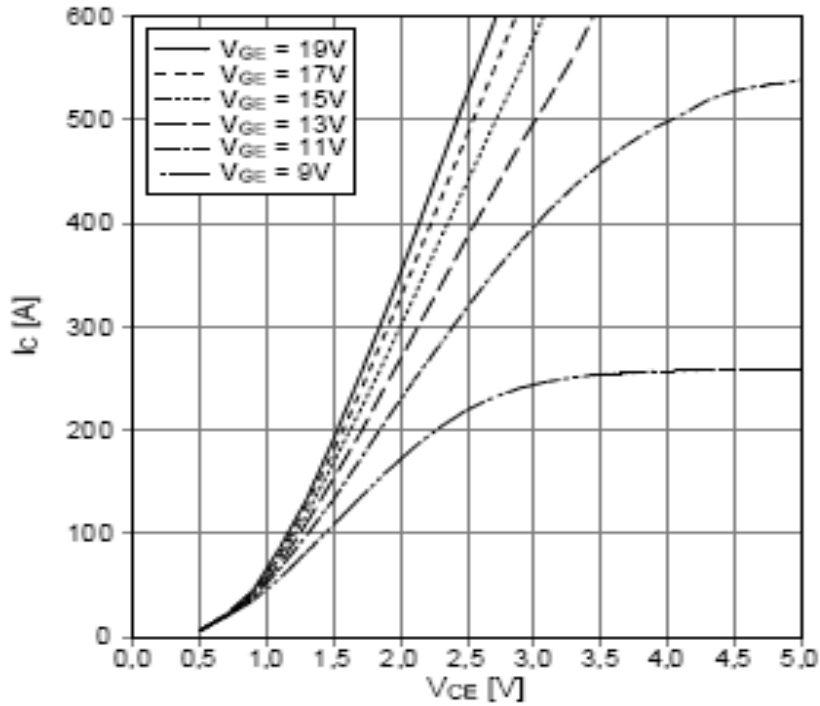
$$V_{GE} = 15 \text{ V}$$





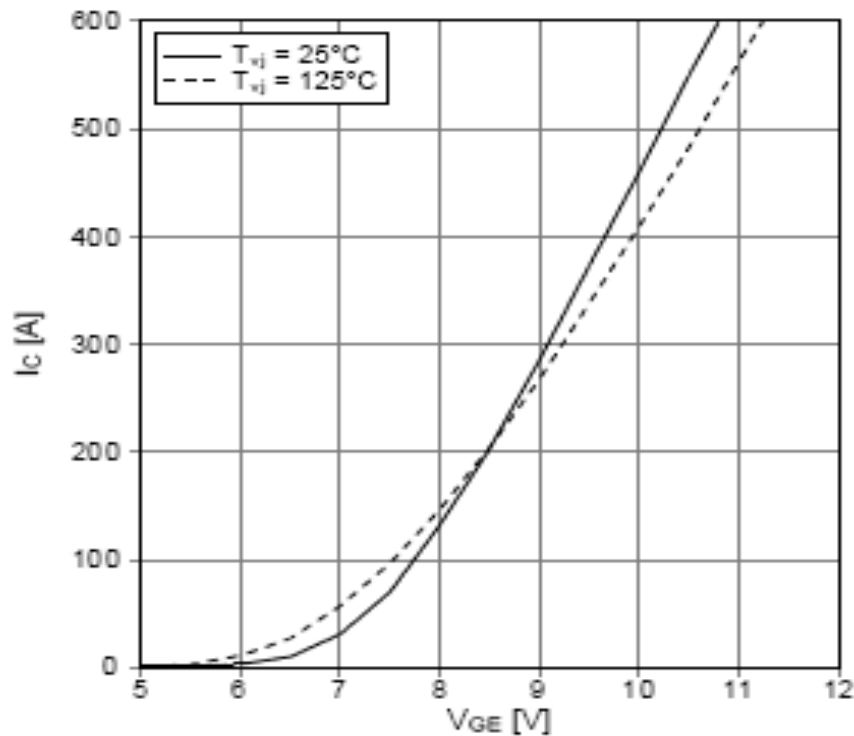
output characteristic IGBT-Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



transfer characteristic IGBT-inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$

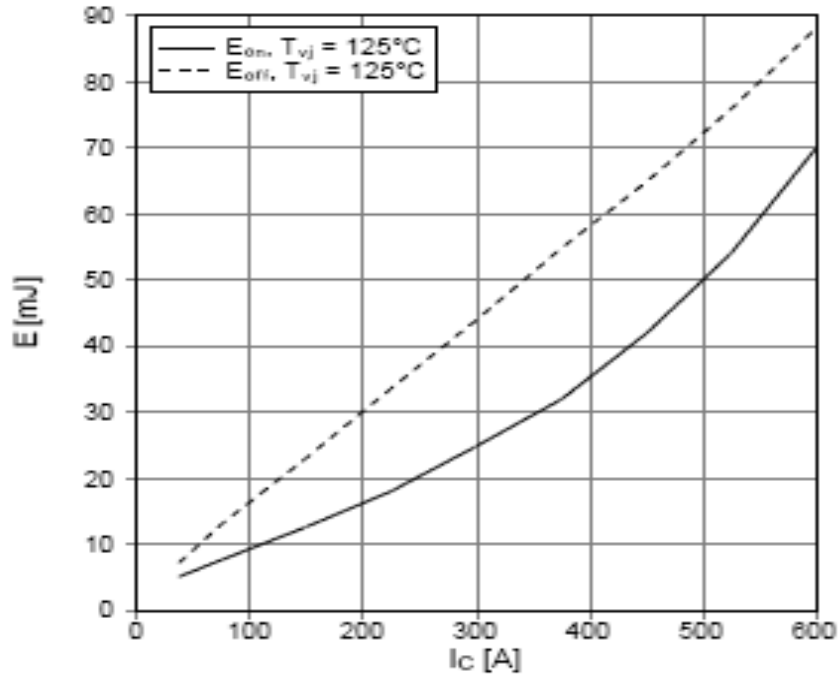




switching losses IGBT-inverter (typical)

$$E_{on} = f(I_c), E_{off} = f(I_c)$$

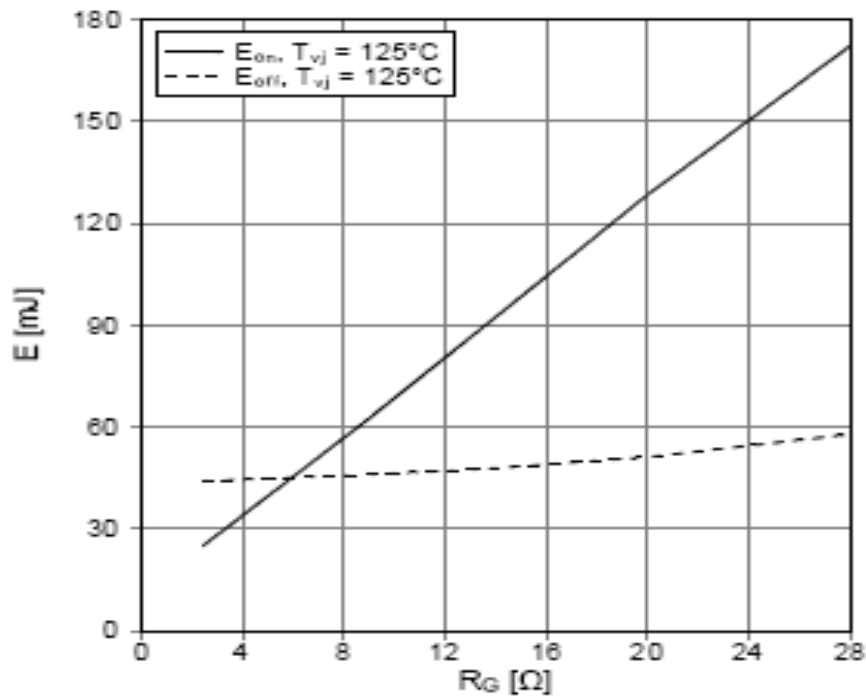
$$V_{GE} = \pm 15 \text{ V}, R_{Gon} = 2.4 \Omega, R_{Goff} = 2.4 \Omega, V_{CE} = 600 \text{ V}$$



switching losses IGBT-Inverter (typical)

$$E_{on} = f(R_G), E_{off} = f(R_G)$$

$$V_{GE} = \pm 15 \text{ V}, I_c = 300 \text{ A}, V_{CE} = 600 \text{ V}$$

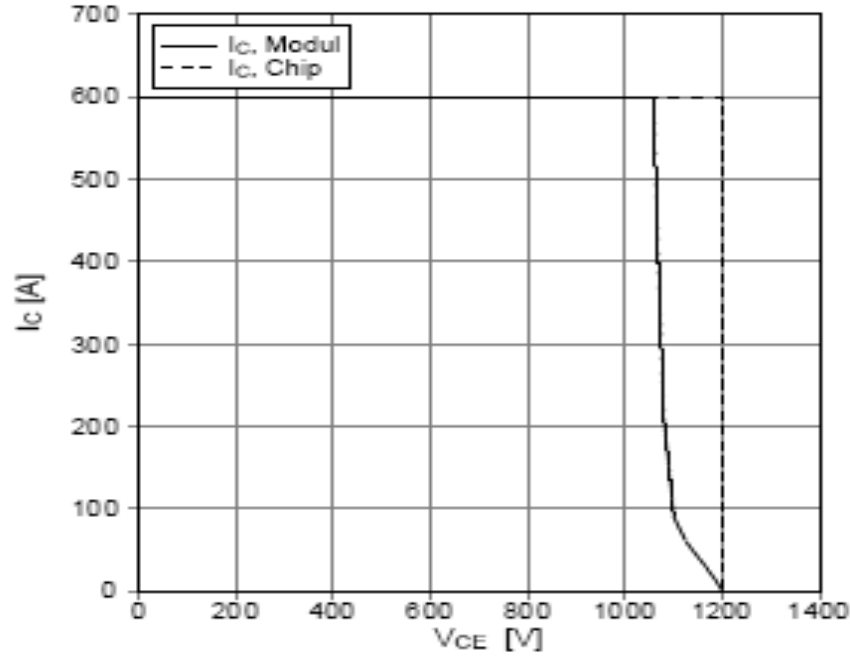




reverse bias safe operating area IGBT-inv. (RBSOA)

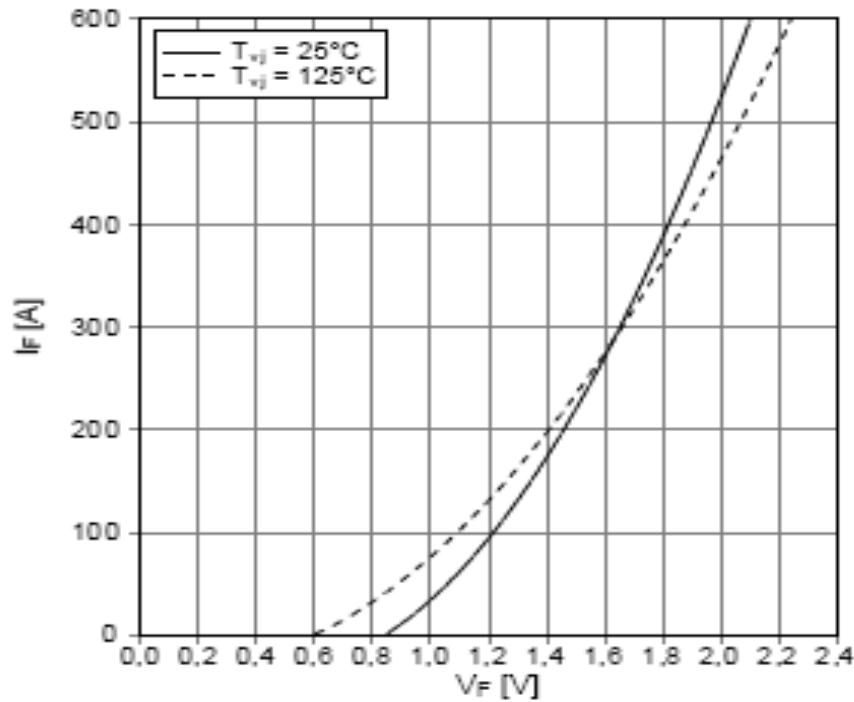
$$I_C = f(V_{CE})$$

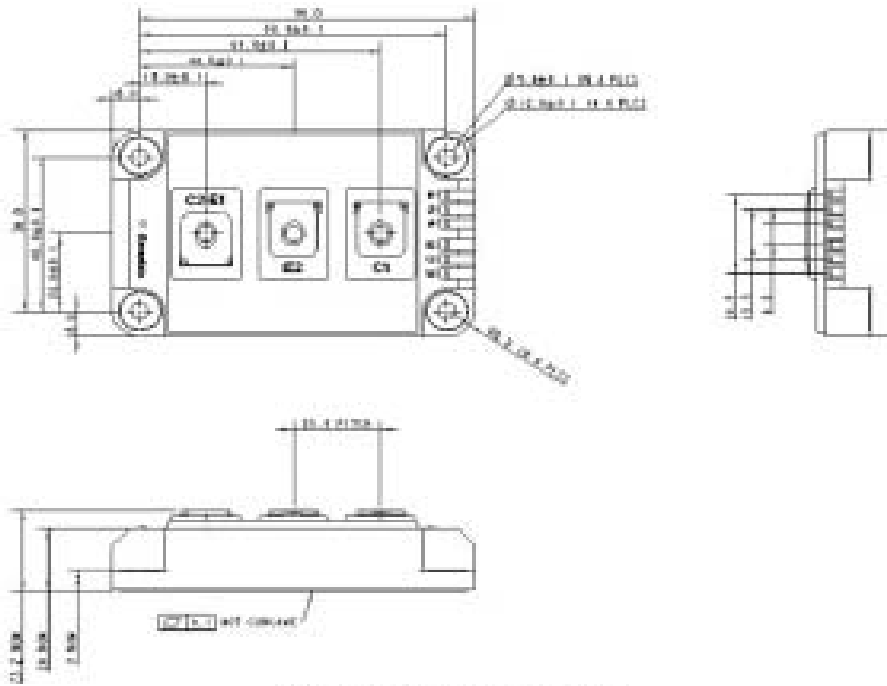
$$V_{GE} = \pm 15 \text{ V}, R_{Goff} = 2.4 \Omega, T_{vj} = 125^\circ\text{C}$$



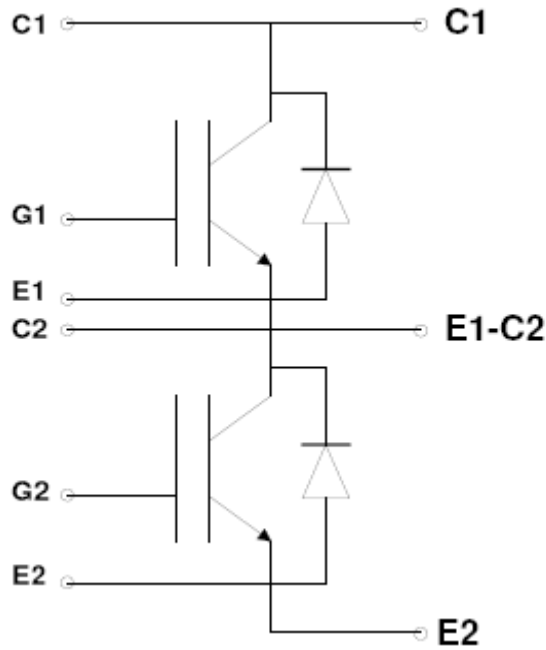
forward characteristic of diode-inverter (typical)

$$I_F = f(V_F)$$





All dimensions in mm



CIRCUIT DIAGRAM